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(54) Title: SEMICONDUCTOR PROCESSING SYSTEM HAVING MULTIPLE DECOUPLED PLASMA SOURCES

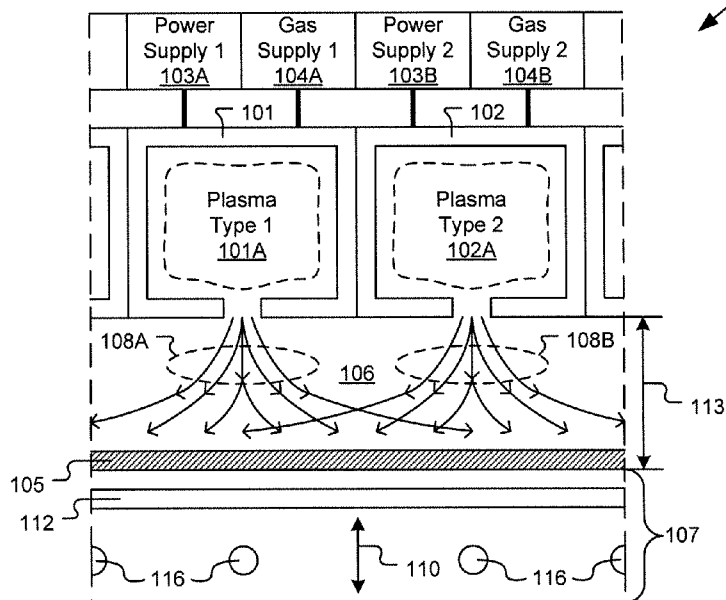


Fig. 2A

(57) Abstract: A semiconductor substrate processing system includes a substrate support defined to support a substrate in exposure to a processing region. The system also includes a first plasma chamber defined to generate a first plasma and supply reactive constituents of the first plasma to the processing region. The system also includes a second plasma chamber defined to generate a second plasma and supply reactive constituents of the second plasma to the processing region. The first and second plasma chambers are defined to be independently controlled.



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